

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S129	1781319	electromagnetic\$3 electro adj magnetic\$3 magnetic\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:06
S130	99226	S129 near3 (resistant resistance seal\$3 shield\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:07
S131	13820	S130 near (layer material)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:08
S132	601469	wafer workpiece	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:08
S133	80107	S132 with (chip die 'IC' integrated adj circuit)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:09
S134	4	S131 with S133	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/22 16:45
S135	15	S131 same S133	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/22 16:45
S136	11	S135 not S134	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/22 16:46
S137	3376	257/295, "E43.001-E43.007", "E27.005-E27.006", "E27.008", "E29.164", "E29.167", "E29.272", "E29.323"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 19:54
S140	877	(428/692,695).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:01

S14 1	909	(428/692,693,694,695).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:00
S14 2	1	252/62.51R-62.51C	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 19:59
S14 3	6136	(252/62.51R-62.51C).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 19:59
S14 4	6498	(428/692,693,694,695,900).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:00
S14 6	9917	(427/127-132).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:01
S14 7	1850	(438/3).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:01
S14 8	2439	(257/295,421,427).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:02
S14 9	73501	((magnetic adj random adj access adj memory) RAM) and shield\$3 and bit daj line and word adj line	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 20:02
S15 0	7562	S149 and (wafer substrate workpiece) with (dicing dice cut cutting slice slicing separat\$3 saw sawing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:04
S15 1	282	S137 and S150	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:04

S15 2	0	S140 and S150	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:04
S15 3	0	S141 and S150	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:04
S15 4	0	S143 and S150	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:05
S15 5	8047	8and S150	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:05
S15 6	0	S144 and S150	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:05
S15 7	0	S145 and S150	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:05
S15 8	1781951	electromagnetic\$3 electro adj magnetic\$3 magnetic\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:06
S15 9	1781951	electromagnetic\$3 electro adj magnetic\$3 magnetic\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:06
S16 0	99265	S159 near3 (resistant resistance seal\$3 shield\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:06
S16 1	99265	S159 and S160	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:07

S16 2	99265	S159 near3 (resistant resistance seal\$3 shield\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:07
S16 3	13824	S162 near (layer material)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:08
S16 4	601695	wafer workpiece	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:09
S16 5	80161	S164 with (chip die 'IC' integrated adj circuit)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 20:10
S16 6	77	S163 with S164	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/25 10:07

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L19	1	memory adj chips and exterior adj (face surface) and memory adj wafer and (magnetically near permeable tray adj magnetic adj fields).clm.	US-PGPUB	OR	OFF	2006/01/25 10:17